NSN 5961-01-012-6543

No Fiig: A110a0

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-012-6543 **Inclosure Material:** Plastic **Overall Length:** 0.780 inches **Overall Height:** 0.180 inches **Overall Width:** 0.280 inches **Component Name And Quantity:** 4 transistor **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** -60.0 collector to base voltage/static/emitter open all transistor and -50.0 collector to emitter voltage/static/base open all transistor and -6.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 600.00 milliamperes source cutoff current all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: pnp **Precious Material And Location:** Terminal plating option gold **Precious Material:** Gold **Test Data Document:** 07187-4014629 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 14 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:**